

**SEMICONDUCTOR  
TECHNICAL DATA**

**KTB1260**

EPITAXIAL PLANAR PNP TRANSISTOR

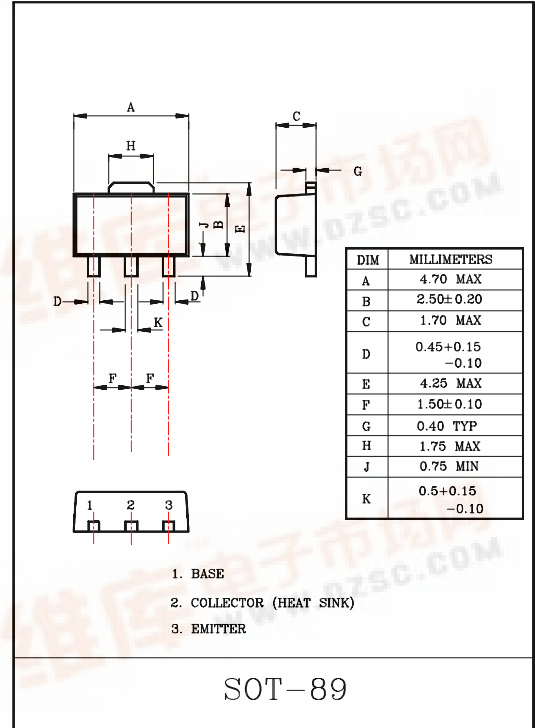
GENERAL PURPOSE APPLICATION.

FEATURES

- 1W (Mounted on Ceramic Substrate).
- Small Flat Package.
- Complementary to KTD1898.

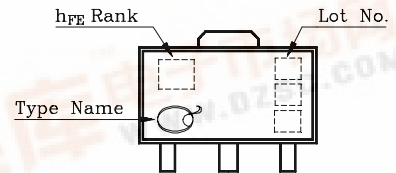
MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	-80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-80	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current	I <sub>C</sub>	-1	A
Emitter Current	I <sub>E</sub>	1	A
Collector Power Dissipation	P <sub>C</sub>	500	mW
	P <sub>C*</sub>	1	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55~150	°C



P<sub>C\*</sub> : KTB1260 mounted on ceramic substrate (250mm<sup>2</sup>x0.8t)

Marking



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> =-60V, I <sub>E</sub> =0	-	-	-1	μA
Emitter Cut-off Current	I <sub>EBO</sub>	V <sub>EB</sub> =-4V, I <sub>C</sub> =0	-	-	-1	μA
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-1mA, I <sub>B</sub> =0	-80	-	-	V
DC Current Gain	h <sub>FE</sub> (Note)	V <sub>CE</sub> =-3V, I <sub>C</sub> =-100mA	70	-	400	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA	-	-	-0.4	V
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =-5V, I <sub>E</sub> =50mA, f=30MHz	-	100	-	MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz	-	25	-	pF

Note : h<sub>FE</sub> Classification O:70~140 , Y:120~240 , GR:200~400